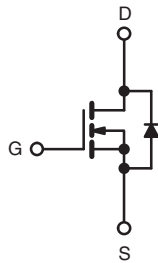
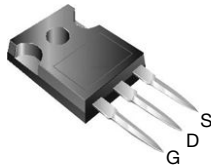


## Power MOSFET

PRODUCT SUMMARY	
$V_{DS}$ (V)	500
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10\text{ V}$ 0.15
$Q_g$ (Max.) (nC)	210
$Q_{gs}$ (nC)	58
$Q_{gd}$ (nC)	100
Configuration	Single

TO-247AC



N-Channel MOSFET

### FEATURES

- Super Fast Body Diode Eliminates the Need for External Diodes in ZVS Applications
- Lower Gate Charge Results in Simpler Drive Requirements
- Enhanced  $dV/dt$  Capabilities Offer Improved Ruggedness
- Higher Gate Voltage Threshold Offers Improved Noise Immunity
- Compliant to RoHS Directive 2002/95/EC



Available  
**RoHS\***  
COMPLIANT

### APPLICATIONS

- Zero Voltage Switching SMPS
- Telecom and Server Power Supplies
- Uninterruptible Power Supplies
- Motor Control Applications

ORDERING INFORMATION	
Package	TO-247AC
Lead (Pb)-free	IRFP31N50LPbF
	SiHFP31N50L-E3
SnPb	IRFP31N50L
	SiHFP31N50L

ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	$V_{DS}$	500	V	
Gate-Source Voltage	$V_{GS}$	$\pm 30$		
Continuous Drain Current	$V_{GS}$ at 10 V	$T_C = 25\text{ }^\circ\text{C}$	31	A
		$T_C = 100\text{ }^\circ\text{C}$	20	
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	124		
Linear Derating Factor		3.7	W/ $^\circ\text{C}$	
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$	460	mJ	
Repetitive Avalanche Current <sup>a</sup>	$I_{AR}$	31	A	
Repetitive Avalanche Energy <sup>a</sup>	$E_{AR}$	46	mJ	
Maximum Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	$P_D$	460	W
Peak Diode Recovery $dV/dt^c$	$dV/dt$	19	V/ns	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to + 150	$^\circ\text{C}$	
Soldering Recommendations (Peak Temperature)	for 10 s	300 <sup>d</sup>		
Mounting Torque	6-32 or M3 screw		10	lbf · in
			1.1	N · m

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 1\text{ mH}$ ,  $R_g = 25\text{ }\Omega$ ,  $I_{AS} = 31\text{ A}$  (see fig. 12).
- $I_{SD} \leq 31\text{ A}$ ,  $dI/dt \leq 422\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150\text{ }^\circ\text{C}$ .
- 1.6 mm from case.

\* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	40	°C/W
Case-to-Sink, Flat, Greased Surface	$R_{thCS}$	0.24	-	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	0.26	


## SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$	500	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$	-	0.28	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	3.0	-	5.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 30\text{ V}$	-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 500\text{ V}$ , $V_{GS} = 0\text{ V}$	-	-	50	$\mu\text{A}$
		$V_{DS} = 400\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 125\text{ }^\circ\text{C}$	-	-	2.0	mA
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 19\text{ A}^b$	-	0.15	0.18	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 50\text{ V}$ , $I_D = 19\text{ A}^b$	15	-	-	S

## Dynamic

Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1.0\text{ MHz}$ , see fig. 5	-	5000	-	pF	
Output Capacitance	$C_{oss}$		-	553	-		
Reverse Transfer Capacitance	$C_{rss}$		-	59	-		
Output Capacitance	$C_{oss}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 1.0\text{ V}$ , $f = 1.0\text{ MHz}$	-	6630	-	
Effective Output Capacitance	$C_{oss\text{ eff.}}$		$V_{DS} = 400\text{ V}$ , $f = 1.0\text{ MHz}$	-	155	-	
Effective Output Capacitance	$C_{oss\text{ eff. (ER)}}$		$V_{DS} = 0\text{ V to } 400\text{ V}^c$	-	276	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}$	$I_D = 31\text{ A}$ , $V_{DS} = 400\text{ V}$ , see fig. 7 and 13 <sup>b</sup>	-	-	210	nC
Gate-Source Charge	$Q_{gs}$			-	-	58	
Gate-Drain Charge	$Q_{gd}$			-	-	100	
Internal Gate Resistance	$R_g$	$f = 1\text{ MHz}$ , open drain		-	1.1	-	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 250\text{ V}$ , $I_D = 31\text{ A}$ , $R_g = 4.3\text{ }\Omega$ , see fig. 10 <sup>b</sup>		-	28	-	ns
Rise Time	$t_r$			-	115	-	
Turn-Off Delay Time	$t_{d(off)}$			-	54	-	
Fall Time	$t_f$			-	53	-	

## Drain-Source Body Diode Characteristics

Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	31	A
Pulsed Diode Forward Current <sup>a</sup>	$I_{SM}$		-	-	124	
Body Diode Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}$ , $I_S = 31\text{ A}$ , $V_{GS} = 0\text{ V}^b$	-	-	1.5	V
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}$ , $I_F = 31\text{ A}$	-	170	250	ns
		$T_J = 125\text{ }^\circ\text{C}$ , $dI/dt = 100\text{ A}/\mu\text{s}^b$	-	220	330	
Body Diode Reverse Recovery Charge	$Q_{rr}$	$T_J = 25\text{ }^\circ\text{C}$ , $I_S = 31\text{ A}$ , $V_{GS} = 0\text{ V}^b$	-	570	860	nC
		$T_J = 125\text{ }^\circ\text{C}$ , $dI/dt = 100\text{ A}/\mu\text{s}^b$	-	1.2	1.8	$\mu\text{C}$
Reverse Recovery Current	$I_{RRM}$	$T_J = 25\text{ }^\circ\text{C}$	-	7.9	12	A
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )				

## Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- $C_{oss\text{ eff.}}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DS}$ .  
 $C_{oss\text{ eff. (ER)}}$  is a fixed capacitance that stores the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DS}$ .

## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

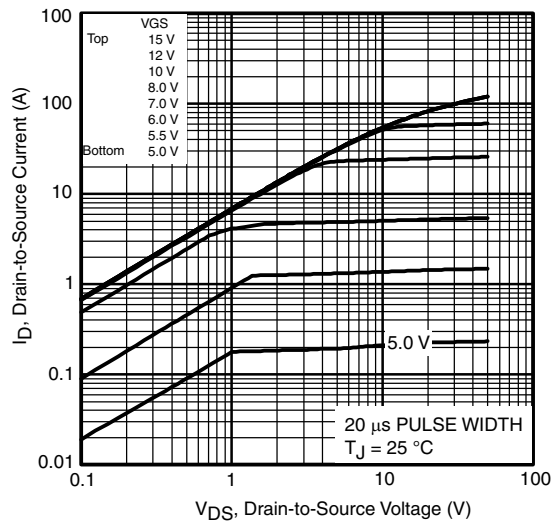


Fig. 1 - Typical Output Characteristics

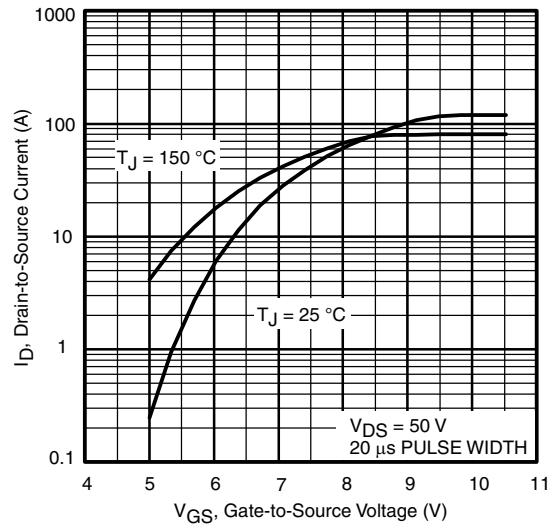


Fig. 3 - Typical Transfer Characteristics

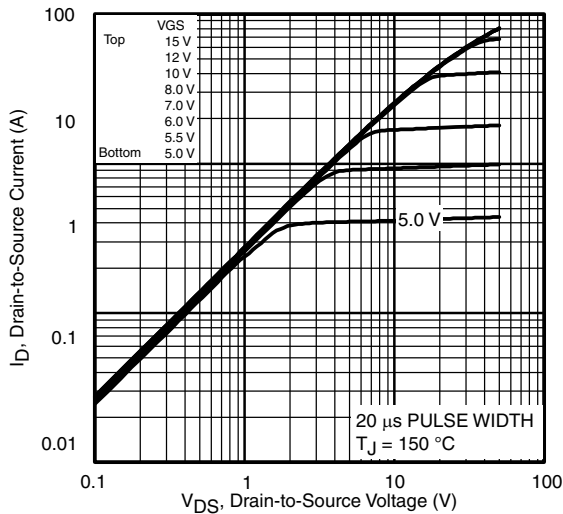


Fig. 2 - Typical Output Characteristics

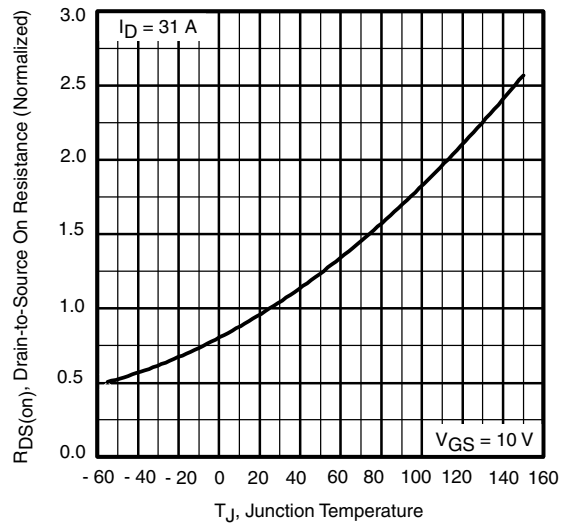


Fig. 4 - Normalized On-Resistance vs. Temperature

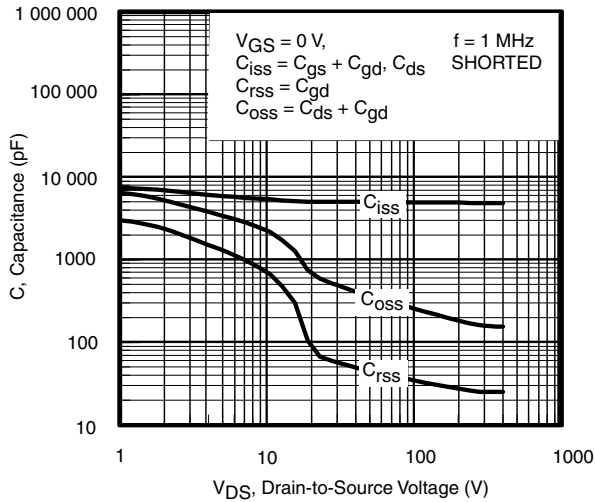


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

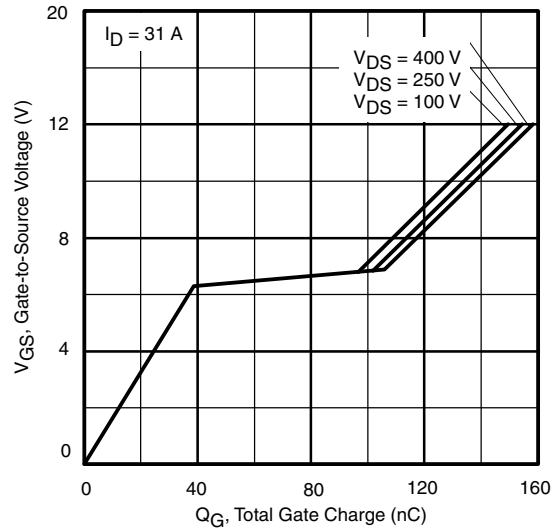


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

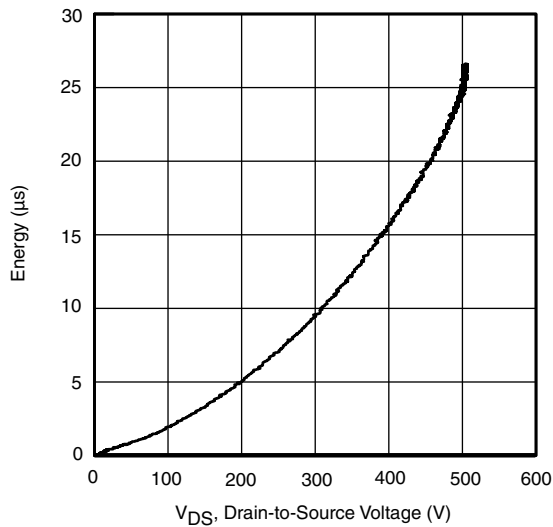


Fig. 6 - Output Capacitance Stored Energy vs.  $V_{DS}$

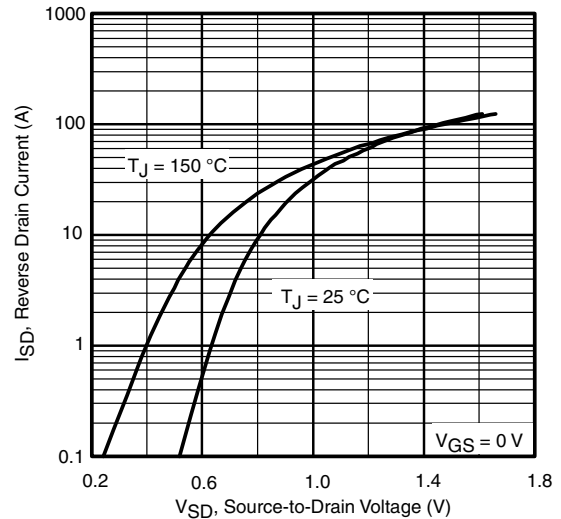
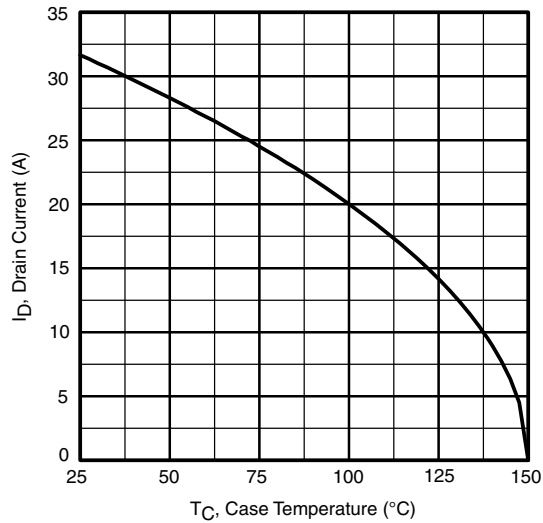
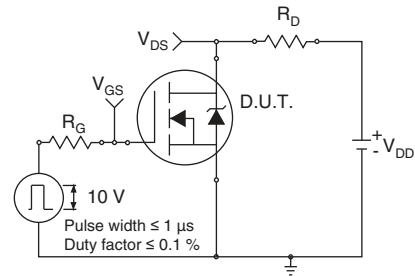


Fig. 8 - Typical Source Drain Diode Forward Voltage



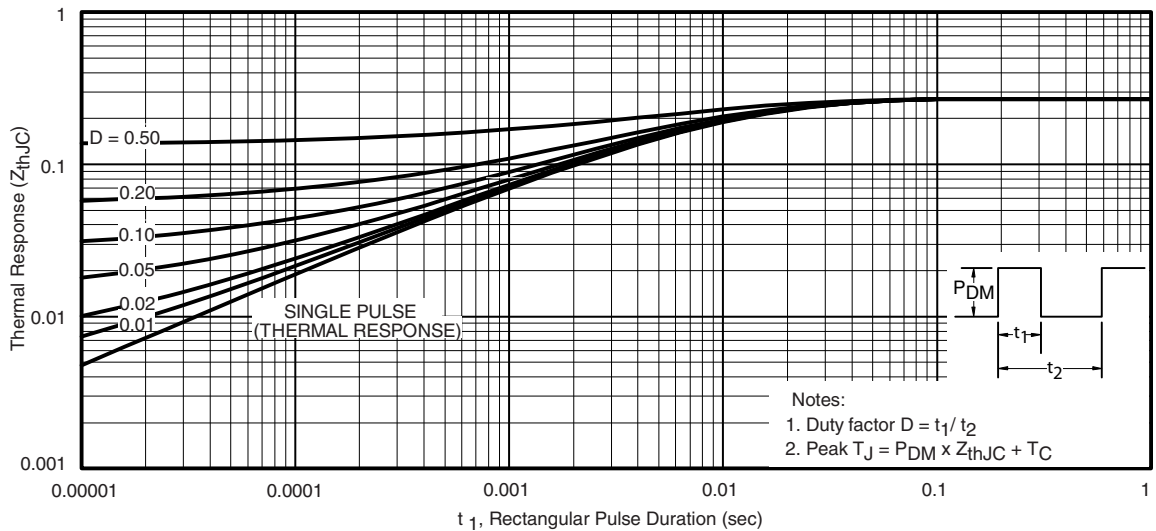
**Fig. 9 - Maximum Drain Current vs. Case Temperature**



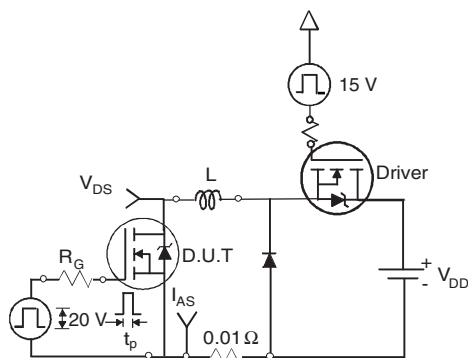
**Fig. 10a - Switching Time Test Circuit**



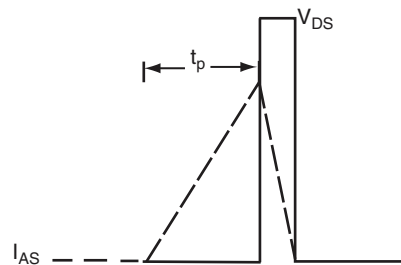
**Fig. 10b - Switching Time Waveforms**



**Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case**



**Fig. 12a - Unclamped Inductive Test Circuit**



**Fig. 12b - Unclamped Inductive Waveforms**

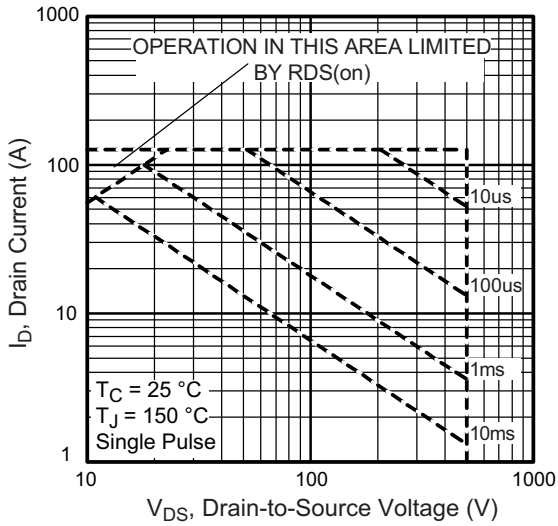


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

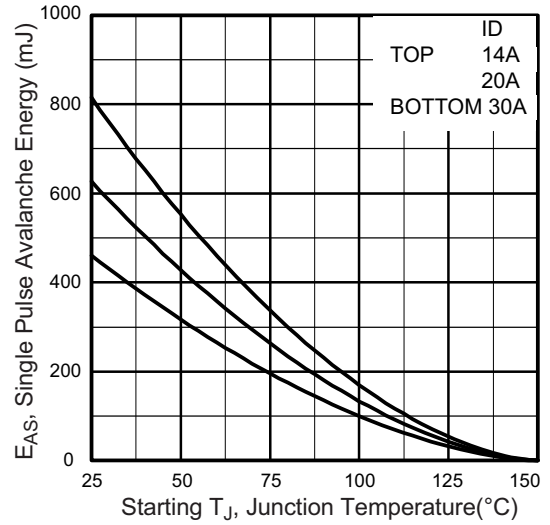


Fig. 12d - Gate Charge Test Circuit

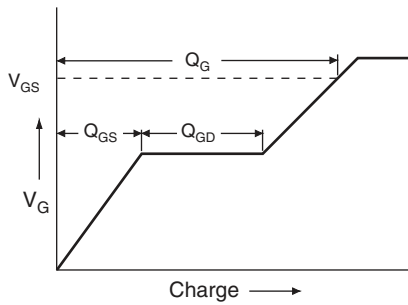


Fig. 13a - Maximum Safe Operating Area

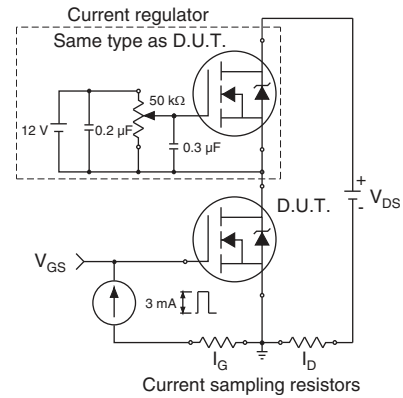
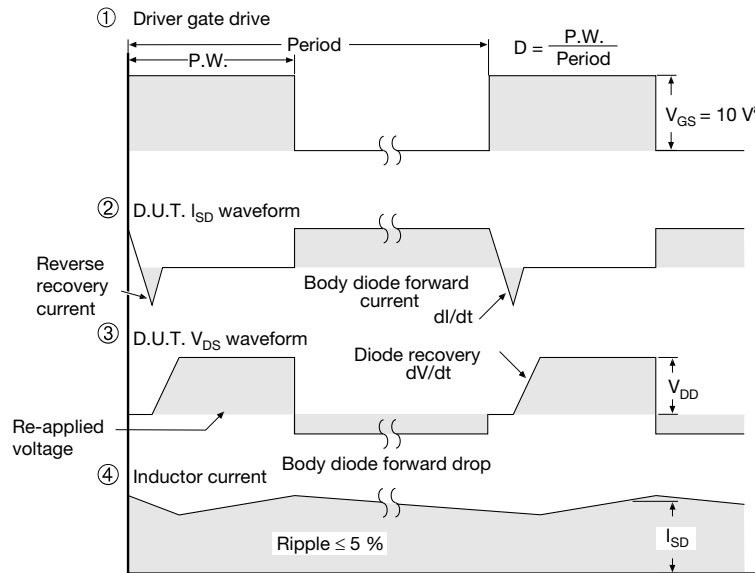
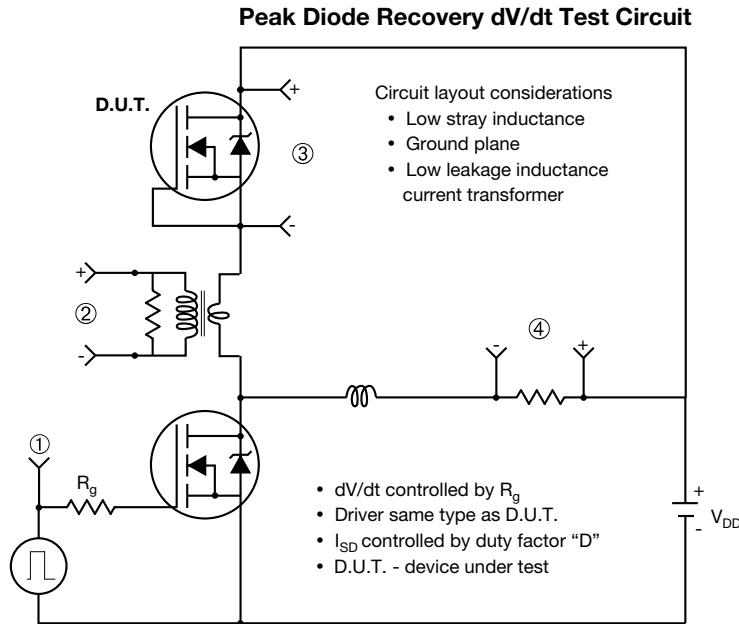


Fig. 13b - Basic Gate Charge Waveform



**Note**  
a.  $V_{GS} = 5\text{ V}$  for logic level devices

**Fig. 14 - For N-Channel**

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# TO-247AC (High Voltage)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.58	5.31	0.180	0.209
A1	2.21	2.59	0.087	0.102
A2	1.17	2.49	0.046	0.098
b	0.99	1.40	0.039	0.055
b1	0.99	1.35	0.039	0.053
b2	1.53	2.39	0.060	0.094
b3	1.65	2.37	0.065	0.093
b4	2.42	3.43	0.095	0.135
b5	2.59	3.38	0.102	0.133
c	0.38	0.86	0.015	0.034
c1	0.38	0.76	0.015	0.030
D	19.71	20.82	0.776	0.820
D1	13.08	-	0.515	-

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D2	0.51	1.30	0.020	0.051
E	15.29	15.87	0.602	0.625
E1	13.72	-	0.540	-
e	5.46 BSC		0.215 BSC	
Ø k	0.254		0.010	
L	14.20	16.25	0.559	0.640
L1	3.71	4.29	0.146	0.169
N	7.62 BSC		0.300 BSC	
Ø P	3.51	3.66	0.138	0.144
Ø P1	-	7.39	-	0.291
Q	5.31	5.69	0.209	0.224
R	4.52	5.49	0.178	0.216
S	5.51 BSC		0.217 BSC	

ECN: X13-0103-Rev. D, 01-Jul-13  
DWG: 5971

**Notes**

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Contour of slot optional.
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body.
4. Thermal pad contour optional with dimensions D1 and E1.
5. Lead finish uncontrolled in L1.
6. Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154").
7. Outline conforms to JEDEC outline TO-247 with exception of dimension c.
8. Xian and Mingxin actually photo.







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